

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
150V	97mΩ @ V _{GS} = 10V	18A
	110mΩ @ V _{GS} = 6V	17A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power Management
- Driving Solenoids
- Motor Control

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.

<https://www.diodes.com/quality/product-definitions/>

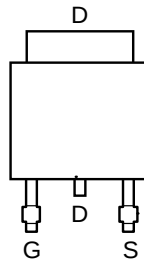
Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminal Connections: See Diagram
- Weight: 0.33 grams (Approximate)

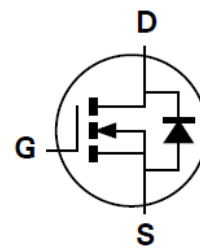
TO252 (DPAK)



Top View



Pin Out Top View



Equivalent Circuit

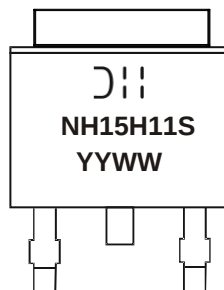
Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH15H110SK3-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

TO252 (DPAK)



D = Manufacturer's Marking
 NH15H11S = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 21 = 2021)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	150	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	I _D	18 12	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	72	A
Maximum Continuous Body Diode Forward Current (Note 7)	I _S	18	A
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)	I _{SM}	72	A
Avalanche Current, L = 3mH	I _{AS}	9	A
Avalanche Energy, L = 3mH	E _{AS}	121.5	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	74	°C/W
Total Power Dissipation (Note 6)	P _D	3.6	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	42	°C/W
Total Power Dissipation (Note 7)	P _D	88	W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	1.7	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	150	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 120V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	70 78	97 110	mΩ	V _{GS} = 10V, I _D = 2A V _{GS} = 6V, I _D = 2A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 2A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	987	—	pF	V _{DS} = 75V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	63	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	34	—	pF	
Gate Resistance	R _g	—	1.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	25.5	—	nC	V _{DS} = 75V, I _D = 4A
Total Gate Charge (V _{GS} = 6V)	Q _g	—	17.8	—	nC	
Gate-Source Charge	Q _{gs}	—	4	—	nC	
Gate-Drain Charge	Q _{gd}	—	10	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	18.1	—	ns	V _{DD} = 75V, V _{GS} = 10V, R _g = 24Ω, I _D = 4A
Turn-On Rise Time	t _r	—	46	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	76.1	—	ns	
Turn-Off Fall Time	t _f	—	58.7	—	ns	
Reverse Recovery Time	t _{RR}	—	41.6	—	ns	I _F = 4A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	65.6	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

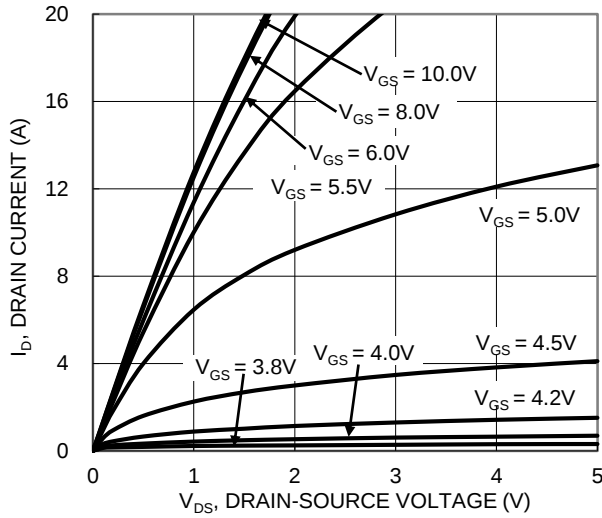


Figure 1. Typical Output Characteristic

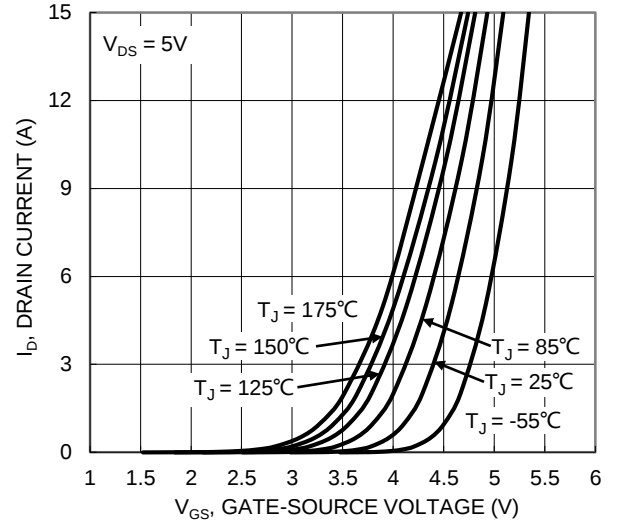


Figure 2. Typical Transfer Characteristic

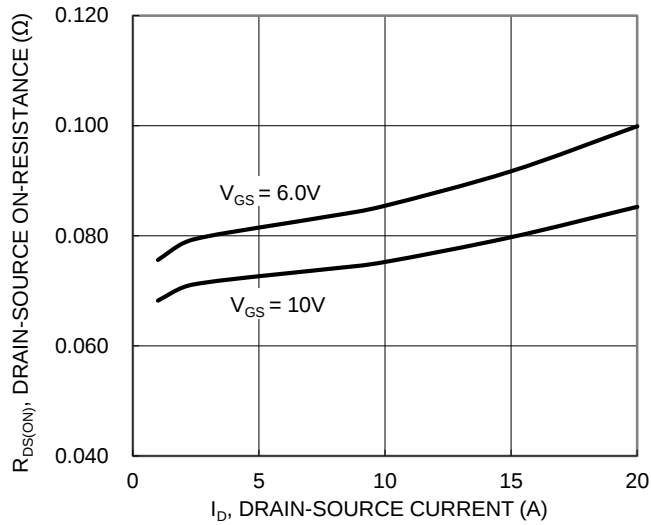


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

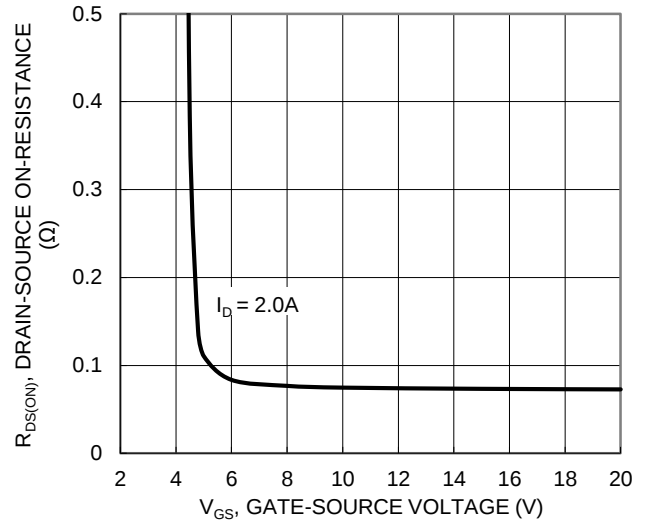


Figure 4. Typical Transfer Characteristic

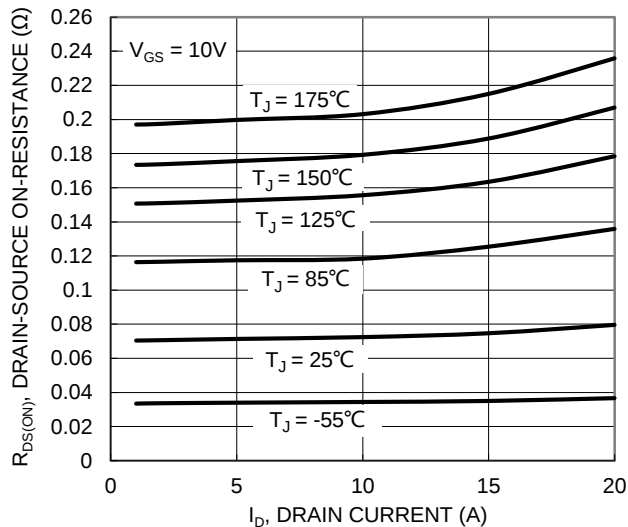


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

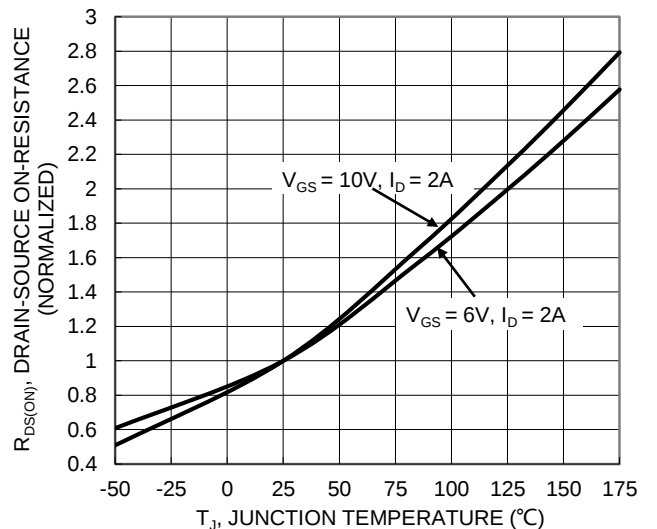


Figure 6. On-Resistance Variation with Junction Temperature

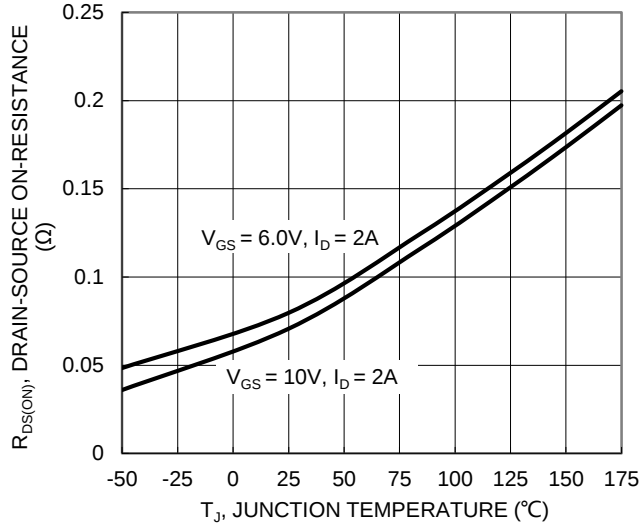


Figure 7. On-Resistance Variation with Junction Temperature

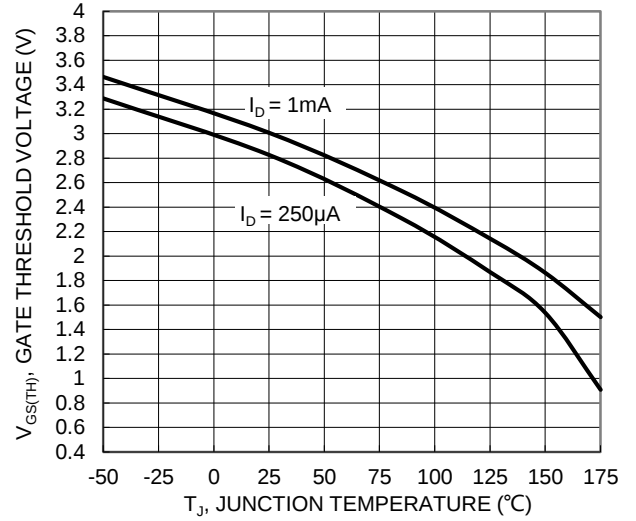


Figure 8. Gate Threshold Variation vs. Junction Temperature

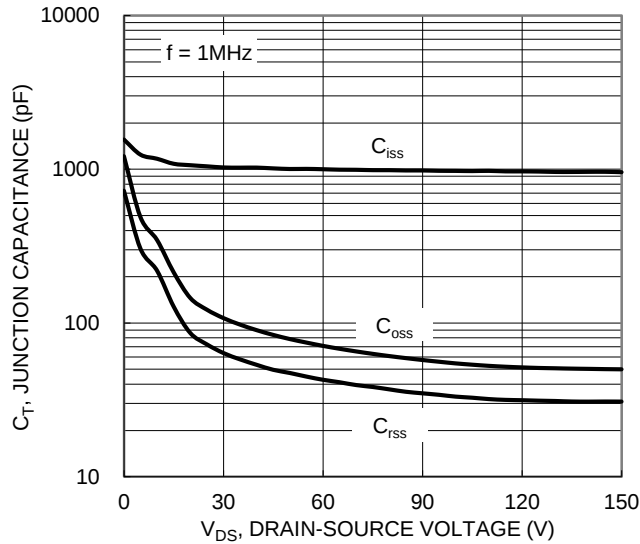


Figure 10. Typical Junction Capacitance

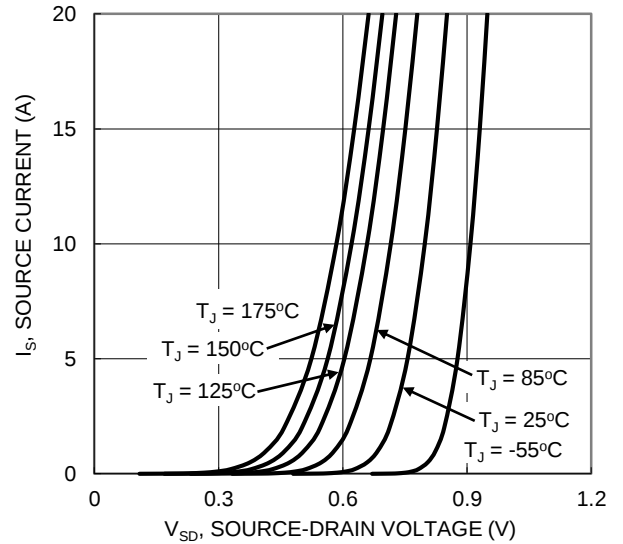


Figure 9. Diode Forward Voltage vs. Current

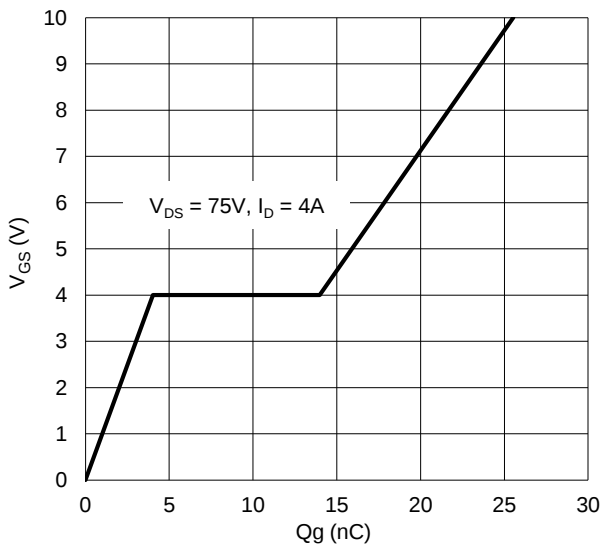


Figure 11. Gate Charge

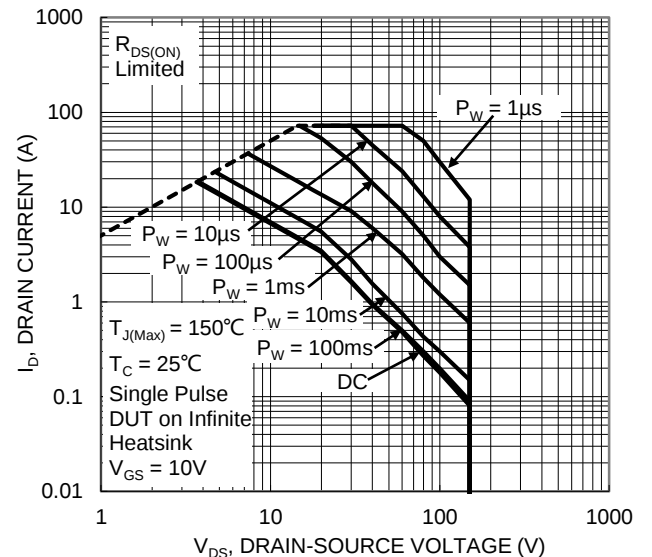


Figure 12. SOA, Safe Operation Area

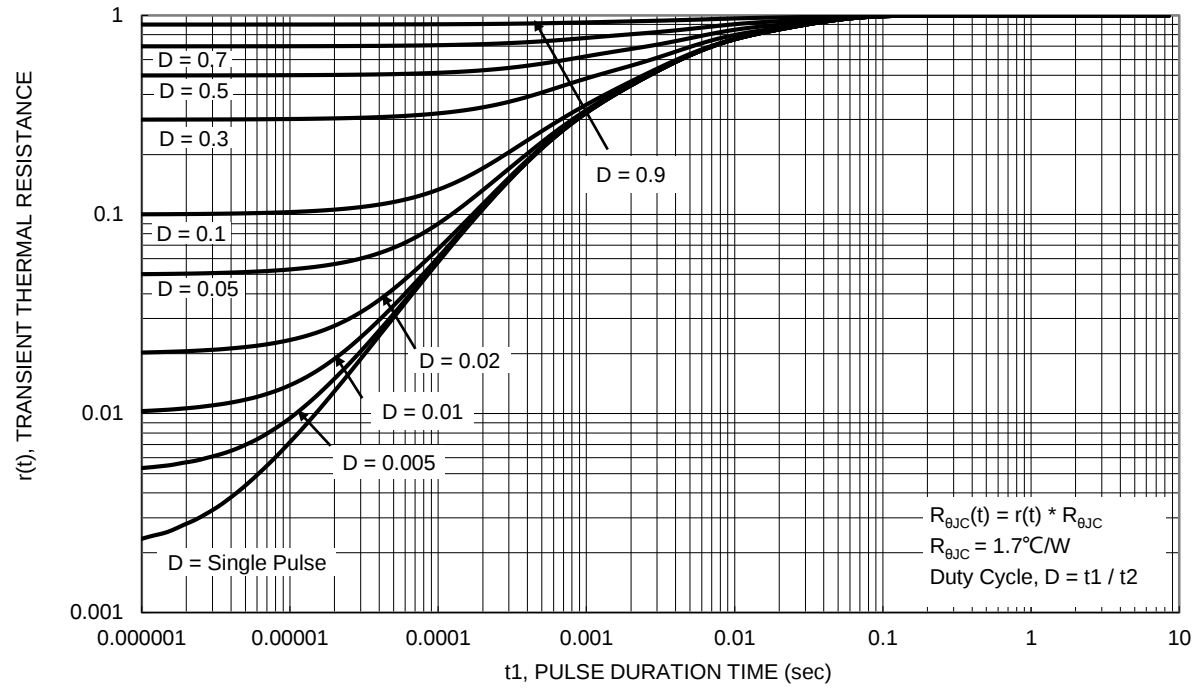
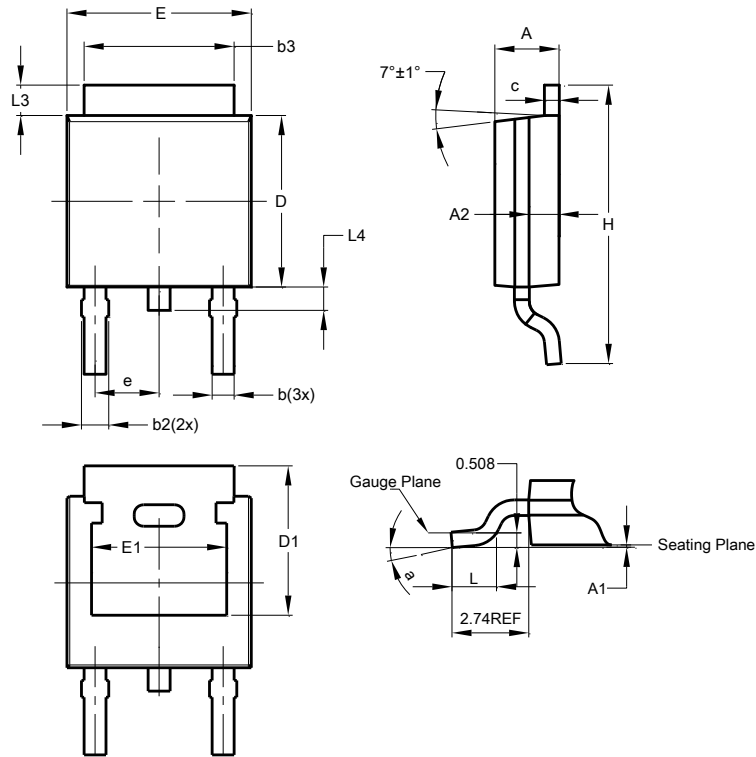


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

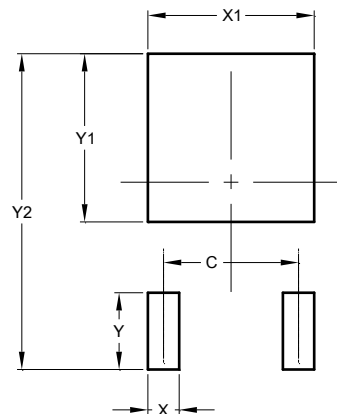


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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